

Dual P-Channel MOSFET

General Description

The WSD40L66DN56 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

The WSD40L66DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

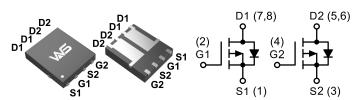
Product Summery

BV _{DSS}	R _{DS(ON)}	I _D
-40V	9.8mΩ	-66A

Applications

- Battery protection
- Load switch
- Uninterruptible Power Supply(UPS)

DFN5X6-8L-EP Pin Configuration



Absolute Maximum Ratings (T_C=25°C, Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-66	А
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-42	А
I _{DM}	Pulsed Drain Current ²	-105	А
E _{AS}	Single Pulse Avalanche Energy ³	146	mJ
P _D @T _C =25°C	Power Dissipation ⁴	1.5	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Units	
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient ¹		25	°C/W	
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case ¹		2.4	°C/W	



Dual P-Channel MOSFET

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250μA	-40			V	
$\Delta BV_{DSS}/\Delta T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA		-0023		V/°C	
D	0	V _{GS} =-10V , I _D =-30A		9.8	13	mO.	
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V , I _D =-20A		15	20	- mΩ	
V _{GS(th)}	Gate Threshold Voltage	\/ -\/ - 250uA	-1.0	-1.6	-2.5	V	
$\Delta V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_{D}=-250\mu$ A		4.74		mV/°C	
	Drain Course Leakage Current	V _{DS} =-32V , V _{GS} =0V , T _J =25°C			1.0		
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-32V , V _{GS} =0V , T _J =55°C			5.0	μA	
I _{GSS}	Gate-Source Leakage Current	V _{DS} =0V , V _{GS} =±20V			±100	nA	
g _{fs}	Forward Transconductance	V _{DS} =-5V , I _D =-18A		24		S	
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f = 1.0MHz		7	14	Ω	
Q_g	Total Gate Charge (-4.5V)	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		27.9			
Q_{gs}	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-12A		7.7		nC	
Q_{gd}	Gate-Drain Charge	1D12A		7.5			
T _{d(on)}	Turn-On Delay Time			40			
T _r	Rise Time	V _{DD} =-15V , V _{GS} =-10V ,		35.2			
T _{d(off)}	Turn-Off Delay Time	$R_G=3.3\Omega$, $I_D=-1A$		100		ns	
T _f	Fall Time			9.6			
C _{iss}	Input Capacitance			3500			
C _{oss}	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f = 1.0MHz		323		pF	
C _{rss}	Reverse Transfer Capacitance			222			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
I _S	Continuous Source Current 1,5	V -V -0V Force Current			-52	^
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			-105	A
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.0	V

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2. The data tested by pulsed , pulse width $\leq 300 us$, duty cycle $\leq 2\%$
- 3. The power dissipation is limited by 150 $^{\circ}\text{C}$ junction temperature
- 4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

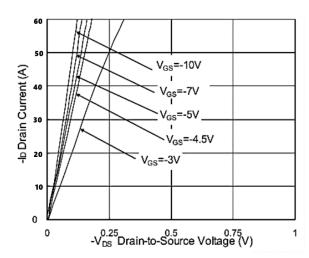


Fig.1 Typical Output Characteristics

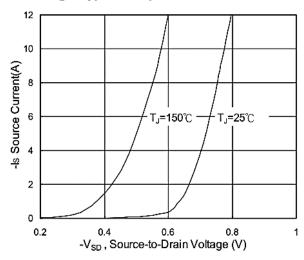


Fig.3 Forward Characteristics Of Reverse

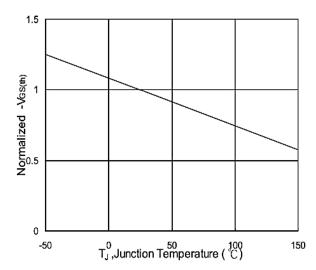


Fig.5 Normalized V_{GS(th)} v.s T_J

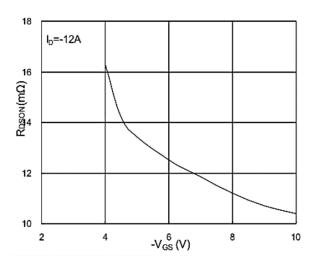


Fig.2 On-Resistance v.s Gate-Source

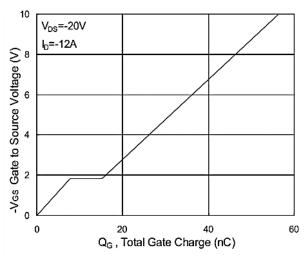


Fig.4 Gate-Charge Characteristics

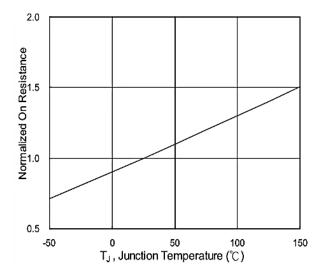
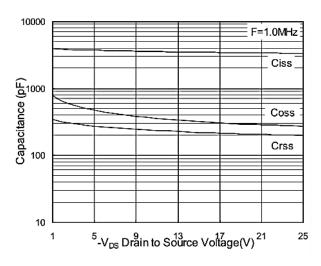


Fig.6 Normalized R_{DSON} v.s T_J



Typical Characteristics (Cont.)



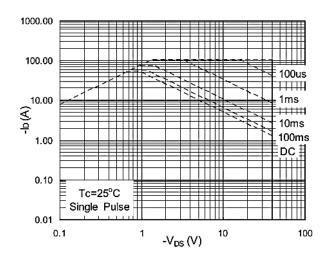


Fig.7 Capacitance

Fig.8 Safe Operating Area

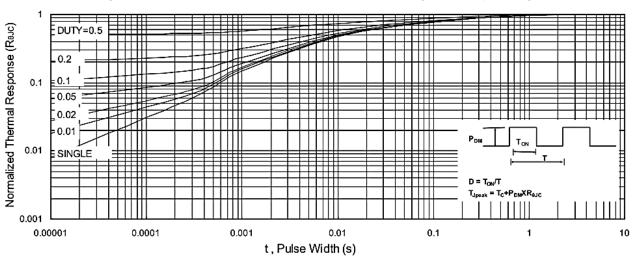


Fig.9 Normalized Maximum Transient Thermal Impedance

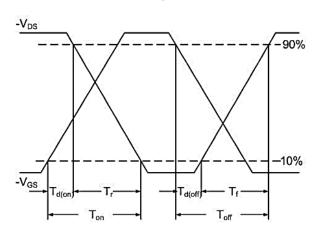


Fig.10 Switching Time Waveform

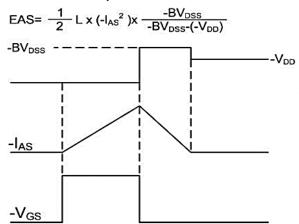
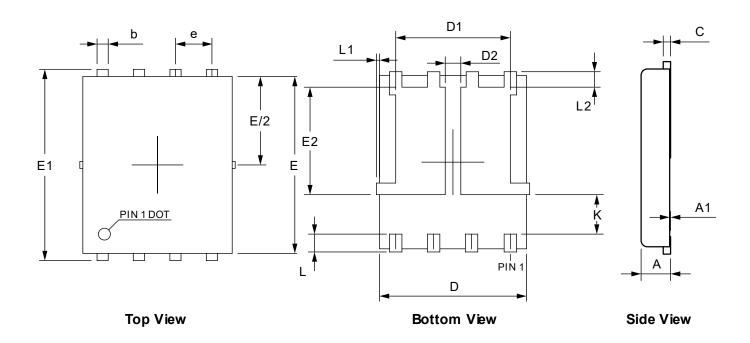


Fig.11 Unclamped Inductive Waveform

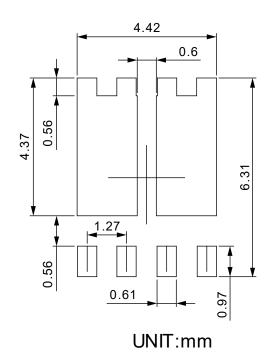
Dual P-Channel MOSFET

Packaging information



SYMBOL	MILLIMETERS		INCHES		
STWIDOL	MIN.	MAX.	MIN.	MAX.	
Α	0.900	1.200	0.035	0.047	
A1	0.000	0.050	0.000	0.002	
b	0.300	0.500	0.012	0.020	
С	0.150	0.300	0.006	0.012	
D	4.800	5.000	0.189	0.197	
D1	3.550	4.550	0.140	0.179	
D2	0.500	0.910	0.020	0.036	
Е	5.650	5.850	0.222	0.230	
E1	5.900	6.200	0.232	0.244	
E2	3.200	3.780	0.126	0.149	
е	1.27	BSC	0.050 BSC		
K	1.100	-	0.043	-	
L	0.500	0.800	0.020	0.031	
L1	0.000	0.150	0.000	0.006	
L2	0.325	0.610	0.013	0.024	

RECOMMENDED LAND PATTERN





Attention

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life–support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high–quality high–reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.
- 9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.